Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	5820	257/758	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/11 14:29
L4	119	(semiconductor or die or dice or chip or IC) and capacitor same (silicon or "Si") near (carbide or "C") and metal with ("C" or carbide)	USPAT	OR	ON	2006/08/11 16:48
L5	4165	257/774	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/11 14:42
L6	1983	257/750	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/11 15:00
L7	119	4 and (semiconductor or die or dice or chip or IC) and capacitor and (silicon or "Si") near (carbide or "C") and metal with ("C" or carbide)	USPAT	OR	ON	2006/08/11 14:47
L8	1433	257/763	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/11 15:09
L9	964	257/754	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/11 15:39

L10	221	257/756	LIC DCDLID:	OB	OFF	2006/09/11 15:40
LIU	331	257/756	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/11 15:48
L11	7	257/E21.664	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/11 15:51
L12	19	257/E27.104	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/11 16:02
L13	4	("20040051129" "6351006" "6500678" "6599806").PN. OR ("7042037").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/08/11 15:55
L14	3771	257/306	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/11 16:04
L15	3785	257/295	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/11 16:34
L16	5133	257/296	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/11 17:02

L17	11	("20010015448" "20030119273" "20030127674" "20030143853" "20040155278" "20040217404" "20050001251" "6351006" "6479849" "6693791" "6924519").PN. OR ("7049650"). URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/08/11 16:43
L18	3	("6372598" "6602543").PN. OR ("6924519").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/08/11 16:47
L19	224	(semiconductor or die or dice or chip or IC) and capacitor same (silicon or "Si") near (carbide or "C") and metal same ("C" or carbide)	USPAT	OR	ON	2006/08/11 17:07
L20	105	19 not 4	USPAT	OR	ON	2006/08/11 16:49
L21	2858	438/238	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/11 17:08
L22	1024	438/244	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/11 17:30
L23	176	(semiconductor or die or dice or chip or IC) and capacitor same (silicon or "Si") near (carbide or "C") and (carbide) with (film or layer)	USPAT	OR	ON	2006/08/11 17:12
L24	45	23 not (4 or 19)	USPAT	OR	ON	2006/08/11 17:12
L25	219	(semiconductor or die or dice or chip or IC) and capacitor same ((silicon or "Si") near (carbide or "C") or "SiC") and (carbide) with (film or layer)	USPAT	OR	ON	2006/08/11 17:16
L26	88	25 not (4 or 19)	USPAT	OR	ON	2006/08/11 17:13
L27	43	25 not (23 or 4 or 19)	USPAT	OR	ON	2006/08/11 17:13
L28	237	(semiconductor or die or dice or chip or IC) and capacitor same ((silicon or "Si") near (carbide or "C") or "SiC") and (carbide) with (film or layer)	US-PGPUB; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/11 17:16

L29	3098	438/3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/11 17:31
S1	151269	(semiconductor or die or chip or IC) and (transistor or mos) or ((silicon near carbide) or ("Si" near "C")) and (meta near carbide) same electrode	USPAT	OR	OFF	2004/12/21 13:09
S2	0	(semiconductor or die or chip or IC) and (transistor or mos) and ((silicon near carbide) or ("Si" near "C")) and (meta near carbide) same electrode	USPAT	OR	OFF	2004/12/21 13:09
S3	0	(semiconductor or die or chip or IC) and (transistor or mos) and ((silicon near carbide) or ("Si" near "C")) and (meta near carbide) and electrode	USPAT	OR	OFF	2004/12/21 13:09
S4	0	(semiconductor or die or chip or IC) and (transistor or mos) and ((silicon near carbide) or ("Si" near "C")) and (meta near carbide)	USPAT	OR	OFF	2004/12/21 13:10
S5	3283	(semiconductor or die or chip or IC) and (transistor or mos) and ((silicon near carbide) or ("Si" near "C"))	USPAT	OR .	OFF	2004/12/21 13:10
S6	91	S5 and (semiconductor or die or chip or IC) and (transistor or mos) and ((silicon near carbide) or ("Si" near "C")) and (("Ti" near "C") or titanium near carbide)	USPAT	OR	OFF	2004/12/21 13:25
S7	89	S5 and (semiconductor or die or chip or IC) and (transistor or mos) and ((silicon near carbide) or ("Si" adj "C")) and (("Ti" adj "C") or titanium near carbide)	USPAT	OR	ON	2004/12/21 13:56
S8	3049	S5 and (semiconductor or die or chip or IC) and (transistor or mos) and ((silicon near carbide) or ("Si" near "C")) and (("Ti" near "C") or titanium near carbide or metal near carbides or conductive carbides)	USPAT	OR	ON	2004/12/21 13:57

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S9	171	S5 and (semiconductor or die or chip or IC) and (transistor or mos) and ((silicon near carbide) or ("Si" near "C")) and (("Ti" near "C") or titanium near carbide or metal near carbides or conductive near carbides)	USPAT	OR	ON	2004/12/21 14:28
S10	182	S5 and (semiconductor or die or chip or IC) and (transistor or mos) and ((silicon near carbide) or ("SiC")) and (("TiC") or titanium near carbide or metal near carbides or conductive near carbides)	USPAT	OR	ON	2004/12/21 14:31
S11	17	S10 not S9	USPAT	OR	ON	2004/12/21 14:29
S12	16	257/758 and ((silicon near carbide) or ("SiC")) with (film or layer) and (("TiC") or titanium near carbide or metal near carbides or conductive near carbides)	USPAT	OR	ON	2004/12/21 14:32
S13	22	257/758 and ((silicon near carbide) or ("SiC")) and (("TiC") or titanium near carbide or metal near carbides or conductive near carbides)	USPAT	OR	ON	2004/12/21 16:24
S14	3295	(semiconductor or die or chip or Ic) and ((silicon near carbide) or ("SiC")) and (("TiC") or titanium near carbide or metal near carbides or conductive near carbides)	USPAT	OR	ON	2004/12/21 14:59
S15	1050	(semiconductor or die or chip or Ic) and ((silicon near carbide) or ("SiC")) with (layer or film) and (("TiC") or titanium near carbide or metal near carbides or conductive near carbides)	USPAT	OR	ON	2004/12/21 16:22
S16	505	S15 and ((silicon near carbide) or ("SiC")) with (layer or film) and (("TiC") or titanium near carbide or metal near carbides or conductive near carbides) and electrode	USPAT	OR	ON	2004/12/21 15:43
S17	545	S15 not S16	USPAT	OR	ON	2004/12/21 15:43

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S18	34	(semiconductor or die or chip or Ic) and ((silicon near carbide) or ("SiC")) with (layer or film) and (("TiC") or titanium near carbide or metal near carbides or conductive near carbides)	JPO	OR	ON	2004/12/21 16:22
S19	15	257/750 and ((silicon near carbide) or ("SiC")) and (("TiC") or titanium near carbide or metal near carbides or conductive near carbides)	USPAT	OR	ON	2004/12/21 16:26
S20	12	257/763 and ((silicon near carbide) or ("SiC")) and (("TiC") or titanium near carbide or metal near carbides or conductive near carbides)	USPAT	OR	ON	2004/12/21 16:26
S21	14	257/763 and ((silicon near carbide) or ("SiC")) and (("TiC") or titanium near carbide or metal near carbides or conductive near carbides or "TaC")	USPAT; JPO	OR	ON	2004/12/21 17:56
S22	3499	(semiconductor or die or chip or IC) and ((silicon near carbide) or ("SiC")) and (("TiC") or titanium near carbide or metal near carbides or conductive near carbides or "TaC")	USPAT; JPO	OR	ON	2004/12/21 16:29
S23	1958	S22 and (gate or source or drain)	USPAT; JPO	OR	ON	2004/12/21 16:29
S24	1213	(semiconductor or die or chip or IC) and ((silicon near carbide) or ("SiC")) with (insulat\$3 or dielectric or film or layer) and (("TiC") or titanium near carbide or metal near carbides or conductive near carbides or "TaC")	USPAT; JPO	OR	ON	2004/12/21 16:29
S25	788	S24 and (gate or source or drain)	USPAT; JPO	OR	ON	2004/12/21 17:14
S26	1	"09252095"	JPO	OR	ON	2004/12/21 17:14
S27	515	(transistor or MOS or FET) and (semiconductor or die or chip or IC) and ((silicon near carbide) or ("SiC")) with (film or layer) and (("TiC") or (titanium or zirconium or hafnium or vanadium or niobium or tantalum) near carbide or "TaC")	USPAT; JPO	OR	ON	2004/12/21 18:01
S28	2967	257/774	USPAT	OR	OFF	2004/12/21 19:39

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S29	3612	257/774	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/21 19:39
S30	5041	257/758	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/21 23:56
S31	307	(semiconductor or die or dice or chip or IC) and capacitor with ("SiC" or silicon near carbide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/21 16:02
S32	84	(semiconductor or die or dice or chip or IC) and capacitor with ("SiC" or silicon near carbide) and (via or hole or plug or interconnect\$3) with ("Si" or silicon or silicide or silicone)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/21 22:55
S33	253	(semiconductor or die or dice or chip or IC) and capacitor same ("SiC" or silicon near carbide) and (via or hole or plug or interconnect\$3) with ("Si" or silicon or silicide or silicone)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/21 22:54
S34	110	(semiconductor or die or dice or chip or IC) and capacitor same (dielectric or insulat\$3) with ("SiC" or silicon near carbide) and (via or hole or plug or interconnect\$3) with ("Si" or silicon or silicide or silicone)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/21 22:55
S35	84	(semiconductor or die or dice or chip or IC) and capacitor with ("SiC" or silicon near carbide) and (via or hole or plug or interconnect\$3) with ("Si" or silicon or silicide or silicone)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/21 22:55
S36	66	S34 not S35	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/21 23:07

S37	143	S33 not S34	US-PGPUB;	OR	ON	2005/07/21 23:09
			USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB			
S38	909	257/754	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/21 23:37
S39	317	257/756	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/21 23:37
S40	0	norble near metal with platinum	USPAT	OR	OFF	2006/02/16 19:52
S41	9481	noble near metal with platinum	USPAT	OR	OFF	2006/02/16 19:53
S42	24	noble near metal with platinum and 257/758	USPAT	OR	OFF	2006/02/16 19:53
S43	538	(semiconductor or die or dice or chip or IC) and ("SiC" or silicon near carbide) with metal\$3 near carbide	USPAT	OR	OFF	2006/02/16 20:03
S44	8	(semiconductor or die or dice or chip or IC) and ("SiC" or silicon near carbide) with metal\$3 near carbide same metal\$3 with electrode	USPAT	OR	OFF	2006/02/16 20:06
S45	9	(semiconductor or die or dice or chip or IC) and ("SiC" or silicon near carbide) same metal\$3 near carbide same metal\$3 with electrode	USPAT	QR	OFF	2006/02/16 20:08
S46	14	(semiconductor or die or dice or chip or IC) and ("SiC" or silicon near carbide) same metal\$3 near carbide same electrode	USPAT	OR	OFF	2006/02/16 20:10
S47	0	(semiconductor or die or dice or chip or IC) and ("SiC" or silicon near carbide) same ("Pt" or platinum) near carbide same electrode	USPAT	OR	OFF	2006/02/16 20:10

S48	3	(semiconductor or die or dice or chip or IC) and ("SiC" or silicon near carbide) same ("Pt" or platinum) near carbide and electrode	USPAT	OR	OFF	2006/02/16 20:11
S49	8	(semiconductor or die or dice or chip or IC) and ("SiC" or silicon near carbide) same ("Pt" or platinum) near carbide	USPAT	OR	OFF	2006/02/16 20:14
S50	115	(semiconductor or die or dice or chip or IC) and ("SiC" or silicon near carbide) and ("Pt" or platinum) near (carbide or "C")	USPAT	OR	OFF	2006/02/16 20:17
S51	19	(semiconductor or die or dice or chip or IC) and ("SiC" or silicon near carbide) same ("Pt" or platinum) near (carbide or "C")	USPAT	OR	OFF	2006/02/16 20:14
S52	18	(semiconductor or die or dice or chip or IC) and ("SiC" or silicon near carbide) and ("Pt" or platinum) near (carbide or "C") same electrode	USPAT	OR	OFF	2006/02/16 20:27
S53	6213	"PtC" or (platinum near carbide) same electrode	USPAT	OR	OFF	2006/02/16 20:27
S54	807	("PtC" or (platinum near carbide)) same electrode	USPAT	OR	OFF	2006/02/16 20:27
S55	66	("PtC" or (platinum near carbide)) near electrode	USPAT	OR	OFF	2006/02/16 20:27
S56	0	(semiconductor or die or dice or chip or IC) and ("SiC" or silicon near carbide) and ("PtC" or (platinum near carbide)) near electrode	USPAT	OR	OFF	2006/02/16 20:27
S57	101	(semiconductor or die or dice or chip or IC) and ("SiC" or silicon near carbide) and ("PtC" or (platinum near carbide))	USPAT	OR	OFF	2006/02/16 20:28
S58	8	(semiconductor or die or dice or chip or IC) and ("SiC" or silicon near carbide) and ("PtC" or (platinum near carbide)) same electrode	USPAT	OR	OFF	2006/02/16 20:29
S59	0	(semiconductor or die or dice or chip or IC) and ("SiC" or silicon near carbide) and (platinum near carbide) same electrode	USPAT	OR	OFF	2006/02/16 20:29

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S60	9	(semiconductor or die or dice or chip or IC) and ("SiC" or silicon near carbide) and (platinum near carbide)	USPAT	OR	OFF	2006/02/16 20:34
S61	1	(semiconductor or die or dice or chip or IC) and ("SiC" or silicon near carbide) and (platinum adj carbide)	USPAT	OR	OFF	2006/02/16 20:35
S62	1	(semiconductor or die or dice or chip or IC) and ("SiC" or silicon near carbide) and (platinum adj carbide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/16 21:08
S63	72	(semiconductor or die or dice or chip or IC) and ("SiC" or silicon near carbide) and (platinum adj (carbide or carbon))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/16 20:36
S64	37	(semiconductor or die or dice or chip or IC) and ("SiC" or silicon near carbide) and (platinum adj (carbide or carbon))	USPAT	OR	OFF	2006/02/16 20:41
S65	2	("SiC" or silicon near carbide) and (platinum adj carbide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/16 20:39
S66	26	(semiconductor or die or dice or chip or IC) and ("SiC" or silicon near carbide) and (platinum adj carbide or ("Pt" adj "C"))	USPAT	OR	OFF	2006/02/16 20:52
S67	0	("SiC" or silicon near carbide) same (platinum adj carbide)	USPAT	OR	OFF	2006/02/16 20:52
S68	1	("SiC" or silicon near carbide) and (platinum adj carbide)	USPAT	OR	OFF	2006/02/16 20:52
S69	1043	("SiC" or silicon near carbide) and (metal adj carbide)	USPAT	OR	OFF	2006/02/16 20:53
S70	221	(semiconductor or die or dice or chip or IC) and ("SiC" or silicon near carbide) same (metal adj carbide)	USPAT	OR	OFF	2006/02/16 20:53
S71	52	(semiconductor or die or dice or chip or IC) and ("SiC" or silicon near carbide) same (metal adj carbide) and platinum	USPAT	OR	OFF	2006/02/16 20:53

S72	1	(semiconductor or die or dice or chip or IC) and ("SiC" or silicon near carbide) and (platinum adj carbide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 21:47
S73	942	257/754	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 22:03
S74	326	257/756	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 22:03